# ESD3V3D5B

Description

ESD3V3D5B is designed to protect voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium.
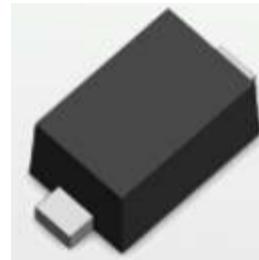
Features

- 100 Watts Peak Pulse Power per Line (tp=8/20μs)
- Operating voltage: 3.3V
- Low leakage current
- Package: SOD-523
- Low clamping voltage
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test
    - Air discharge: ±15kV
    - Contact discharge: ±8kV
  - IEC61000-4-4 (EFT) 40A (5/50ηs)

Functional Diagram
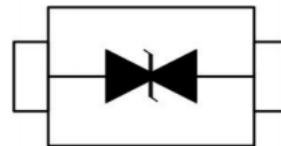
Applications

- Cell Phone Handsets and Accessories
- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation
- Peripherals
- Pagers

Absolute Maximum Ratings(Tamb=25 ℃ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	P_{PP}	100	Watts
ESD per IEC 61000−4−2 (Air)	V_{ESD}	±15	KV
ESD per IEC 61000−4−2 (Contact)		±8	KV
Lead Soldering Temperature	TL	260 (10 sec)	°C
Operating Temperature Range	T_J	-55 to +125	°C
Storage Temperature Range	T_{STJ}	-55 to +150	°C

Electrical Characteristics (TA = 25 ℃ unless otherwise noted)

| Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Reverse Stand-off Voltage	VRWM				3.3	V
Reverse Breakdown Voltage	VBR	It = 1mA	4			V
Reverse Leakage Current	IR	VR =VRWM			1	μA
Clamping Voltage	VC	IPP=1A, tP = 8/20μs			7	V
Clamping Voltage	VC	IPP=8A, tP = 8/20μs			12	V
Junction Capacitance	CJ	VR=0V, f = 1MHz			10	pF

Characteristics Curves

Figure 1- Power Derating Curve
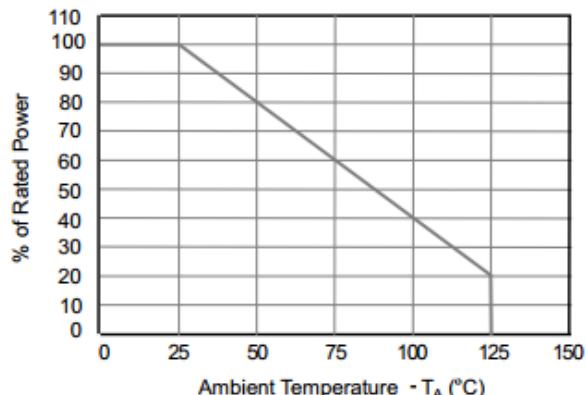
Figure 2- ESD Pulse Waveform
(according to IEC 61000-4-2)
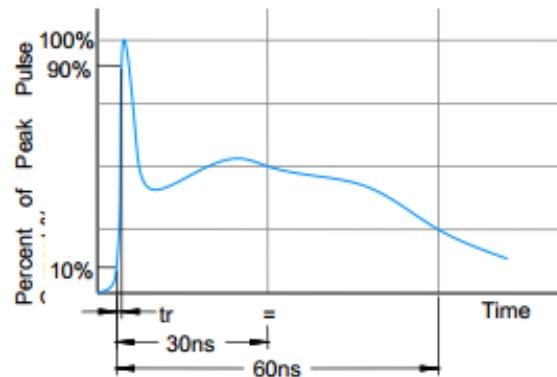
Figure3- 8/20μs Pulse Waveform
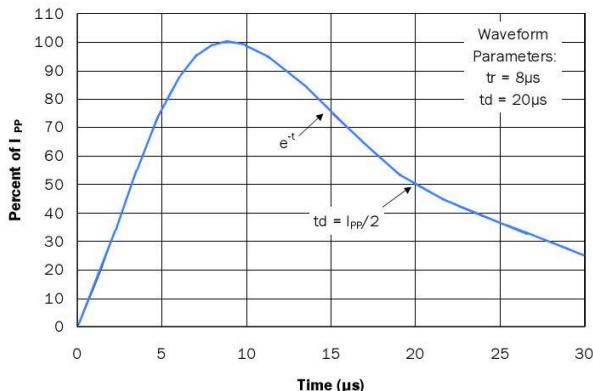
ACKAGE OUTLINE DIMENSIONS in millimeters (inches) :SOD523
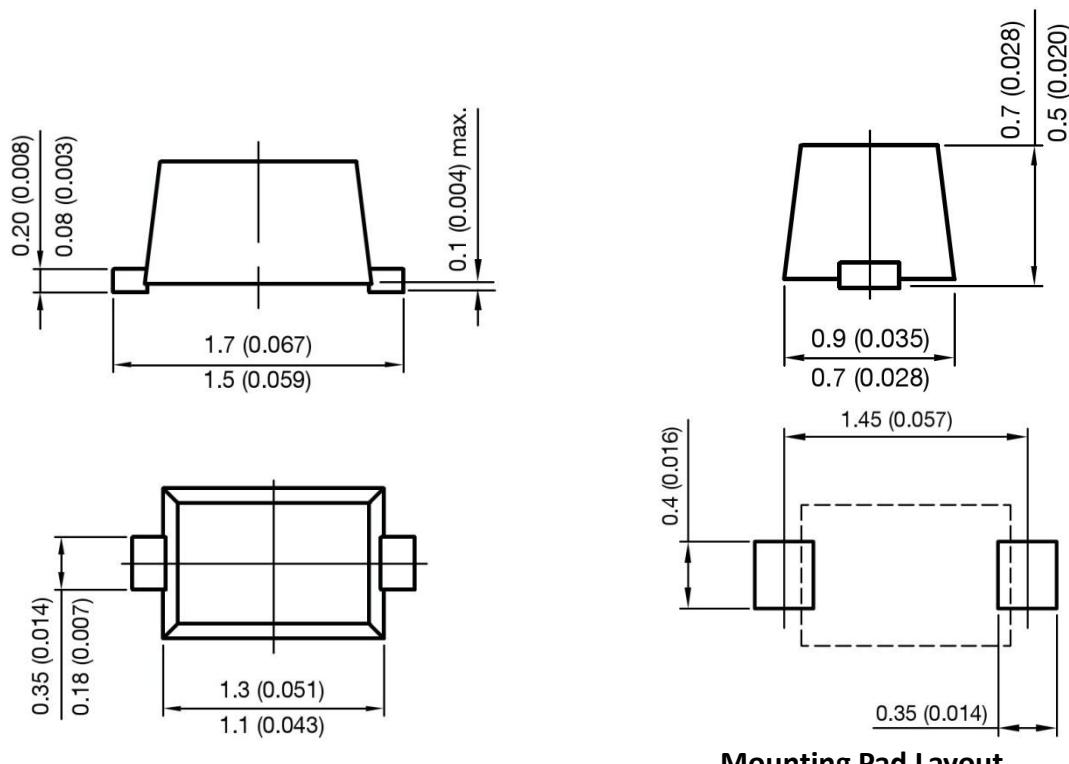
Mounting Pad Layout

Disclaimer

Specifications are subject to change without notice.

The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.

Users should verify actual device performance in their specific applications.